

Geometries, Stabilities, and Growth Patterns of the Bimetal Mo₂-doped Si_n (n = 9–16) Clusters: A Density Functional Investigation

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The behaviors of the bimetal Mo–Mo doped cagelike silicon clusters Mo₂Si_n at the size of n = 9–16 have been investigated systematically with the density functional approach. The growth-pattern behaviors, relative stabilities, and charge-transfer of these clusters are presented and discussed. The optimized geometries reveal that the dominant growth patterns of the bimetal Mo–Mo doped on opened cagelike silicon clusters (n = 9–13) are based on pentagon prism MoSi₁₀ and hexagonal prism MoSi₁₂ clusters, while the Mo₂ encapsulated Si_n (n = 14–16) frames are dominant growth behaviors for the large-sized clusters. The doped Mo₂ dimer in the Si_n frames is dissociated under the interactions of the Mo₂ and Si_n frames which are examined in term of the calculated Mo–Mo distance. The calculated fragmentation energies manifest that the remarkable local maximums of stable clusters are Mo₂-doped Si_n with n = 10 and 12; the obtained relative stabilities exhibit that the Mo₂-doped Si₁₀ cluster is the most stable species in all different sized clusters. Natural population analysis shows that the charge-transfer phenomena appearing in the Mo₂-doped Si_n clusters are analogous to the single transition metal Re or W doped silicon clusters. In addition, the properties of frontier orbitals of Mo₂-doped Si_n (n = 10 and 12) clusters show that the Mo₂Si₁₀ and Mo₂Si₁₂ isomers have enhanced chemical stabilities because of their larger HOMO–LUMO gaps. Interestingly, the geometry of the most stable Mo₂-Si₉ cluster has the framework which is analogous to that of Ni₂Ge₉ cluster confirmed by recent experimental observation (Goicoechea, J. M.; Sevov, S. C. *J. Am. Chem. Soc.* **2006**, *128*, 4155).

1. Introduction

Silicon and germanium clusters have been studied extensively by both theoretical and experimental techniques because they may be employed as the building blocks for developing new silicon-based nanomaterials with tunable properties.^{1–21} After the transition metal (TM) is doped into the silicon frame, the TM doped silicon clusters exhibit a variety of geometrical arrangement and electronic properties,^{21–34} tend to form closed-shell electronic structures that show the extraordinary stabilities comparing with the pure species, and contribute to generating novel transition metal encapsulated clusters with novel properties.

In a pioneering series of experimental measurements, Beck¹⁸ generated mixed transition metal silicide clusters of composition TM@Si_nH_x (TM=Cu, Mo, W) by laser vaporization supersonic expansion technique. These cluster units were found to be more stable toward photofragmentation than pure Si_n clusters of similar size. Scherer et al.¹² produced mixed transition metal silicides by time-of-flight mass spectroscopy and studied the electronic states of CuSi, AgSi, and AuSi dimers by measuring their laser absorption spectra. In addition, the VSi and NbSi dimers have been investigated by matrix-isolated ESP spectroscopy.⁵ Recently, the previous works on the stable TMSi_n

(TM=Cr, Mo, W, Hf, Ta, W, Re, Ir; n = 14, 13, 12, 11, 9)¹⁹ and TbSi_n[–] (6 ≤ n ≤ 16)²² were studied experimentally by aid of various technical methods. The photoelectron spectra of the chromium-doped silicon cluster anions, CrSi_n[–] (n = 8–12),²¹ were measured. From the measurements of vertical detachment energies, enhanced stability was found for the unit CrSi₁₂. The experimental results on vertical detachment energies indicate that the CrSi₁₂ unit has enhanced stability with chromium atom being encapsulated inside the Si₁₂ cage.²¹

Stimulated by these experiment observations, many computational investigations have been performed for one transition metal doped silicon clusters.^{22–35} Although the mixed Cu_mSi_n clusters were detected by mass spectroscopy experimentally,²⁰ to our knowledge, no detailed theoretical investigations on the mixed transition metals TM_n (n > 1) doped silicon clusters have been performed until now. In order to reveal the unusual properties of the bimetal Mo₂-doped silicon clusters, the main objective of this research, therefore, is to provide a detailed investigation of the equilibrium geometries, relative stabilities, fragmentation energies [D(n, n – 1)], the atomic averaged binding energies [E_b(n)], charge transfer of the Mo₂Si_n clusters, and to explore the growth-pattern mechanisms of the polymetal doped silicon clusters, which can provide significant help in the quest for such kind of cluster assembled materials.

2. Computational Details

In order to provide the accurate and reliable results, we carry out the detailed density functional theory (DFT) investigation

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TABLE 1: The Calculated Bond Length Dissociation Energy, Frequency, and Electronic State for the Si₂, Mo₂, and MoSi Clusters

clusters	method	bond length(Å)	dissociation energy(eV)	frequency (cm ⁻¹)	electronic state
Si ₂	B3LYP	2.35	2.62	445.7	³ Σ _g ⁻
	EXP ^a	2.25	3.22	511.0	³ Σ _g ⁻
	ADF ^b	2.31	3.30	463.5	³ Σ _g ⁻
Mo ₂	B3LYP	1.98	1.75	562.0	¹ Σ _g ⁺
	LSDA ^c	1.95	2.17	520.0	¹ Σ _g ⁺
	EXP ^d	1.94	2.19	477.0	¹ Σ _g ⁺
MoSi	B3LYP	2.40	1.90	316.6	⁵ Π
	B3LYP ^e	2.36	2.08		⁵ Π

^a Ref 40. ^b Ref 29. ^c Ref 44. ^d Ref 45. ^e Ref 24.

on the Mo–Mo doped silicon clusters at the size range ($9 \leq n \leq 16$). The equilibrium geometries and electronic properties of the Mo₂ doped silicon clusters are performed by DFT with the unrestricted B3LYP exchange-correlation potential^{36,37} and an effective core potential LanL2DZ basis sets. The standard LanL2DZ basis sets³⁸ are employed to provide an effective way to reduce difficulties in calculations of two-electron integrals caused by heavy transition metal Mo atoms. All computational works are carried out by Gaussian 03 package.³⁹ The polarization basis sets are not considered in this work because our previous work³² showed that they are insignificant to our results. Here is the more information about what structures should be considered for our clusters. It should be pointed out that a small number of structures were tried for each size *n*, and that these structures were taken from prior studies of singly-TM doped Si_{*n*} clusters.^{3,8,11,14,25–32} For clusters containing 12–18 atoms, as considered here, there are a very large number of local minima for each size, and it is in no way obvious that the small subset chosen contains the best structures. Therefore, in this study we try to examine if the localization of Mo atoms upon/into silicon clusters changes the major rearrangement of the geometry framework of Si_{*n*} clusters (or cages) as well as to reveal the striking change in properties due to the inserting of the various metals. Fortunately, previous theoretical results on MSi_{*n*} (M=W and Re) and MGe_{*n*} (M=W, Cu, and Ni) are available^{3,8,11,14,25–32} and can be considered into our structure optimization. For each stationary point of a cluster, the stability is reassured by the calculated harmonic vibrational frequencies. If the unstable geometry with one imaginary frequency is found, a relaxation along the coordinates of the imaginary vibrational mode is rearranged until a true local minimum is finally reached. Therefore, geometries and total energies for each stable cluster and its stable isomers actually correspond to the local minima. As the number of isomers is increased quickly with the cluster size, it is very difficult to obtain the global minimum simply according to the calculated total energies of the isomers.

In order to obtain the most possible stable Mo₂Si_{*n*} (*n* = 9–16) clusters, some previous available theoretical or experimental results are considered first, then the equilibrium geometry is determined by varying the geometry starting from high-symmetry structure to low-symmetry structure. This leads to a limited number of possible stable structures for each size of cluster.

To test the reliability of our calculations, the Si₂, Mo₂, and MoSi molecules are carried out, and the calculated bond lengths, vibrational frequencies, and dissociation energies are illustrated in Table 1. From Table 1, one can find that the calculated results of the Si₂, Mo₂, and MoSi clusters are in good agreement with the reported theoretical and experimental results that are available.^{24,40–44} This examination of equilibrium bond lengths and angles leads to deviations typically within 1–6%. Since

the calculated results also depend on the pseudopotentials, our study can be considered as preliminary and qualitative in nature. On the basis of the calculated results, it should be pointed out that the dissociation energy of the MoSi cluster is smaller than that of the Si₂ cluster, but bigger than that in the free Mo₂ molecule. This result reflects that in the Mo₂Si_{*n*} clusters the Si–Si interaction is stronger than the Mo–Si and Mo–Mo interactions and plays a dominant role in stabilizing the Mo₂–Si_{*n*} clusters.

3. Results and Discussions

3.1. Geometries and Stabilities. Mo₂Si₉. Considering of all the possible geometries, three stable isomers have been identified for the Mo₂Si₉ cluster as shown in Figure 1. On the basis of the calculated total energies, which are listed in Table 2, we find that the 9a isomer is slightly higher in total energy than the 9b isomer does; therefore, the 9b isomer is more stable than the 9a isomer. Interestingly, structure 9a and structure 9b have different equilibrium geometries and can be considered as the degenerated isomers with different framework of silicon clusters because the energetic difference between these two isomers is very small. In addition, both 9a and 9b isomers can be described as one Mo atom being surface capped on the MoSi₉ frame after other Mo atom being encapsulated into the Si₉ frame. With respect to the 9c isomer, the optimized equilibrium geometry has the frame which is analogous to the experimental structure of the Ni₂Ge₉ cluster³³ and can be described as one Mo being surface capped on the antiprism MoSi₉ frame. However, the total energy of the 9c isomer is distinctly higher than that of the 9a and 9b isomers, which indicates that the 9c isomer is less stable than the 9a and 9b isomers. Consequently, the 9b isomer with the encapsulated Mo atom having tendency to terminate the dangling bonds of the Si₉ frame and trying to interact with all silicon atoms directly with unequivalent bond lengths is selected as the most stable isomer and the ground state for cluster Mo₂Si₉. In addition, from our optimization the most stable Mo₂Si₉ 9b geometry is different from the experimental geometry of the Ni₂Ge₉ cluster.³³

Mo₂Si₁₀. Four possible geometries of the Mo₂Si₁₀ cluster (Figure 1), which are described as the pentagonal antiprism C_s Mo₂Si₁₀ 10a, two pyramidal Si₄ capped rhombus Mo₂Si₂ C_s 10b, the Mo surface capped sandwich-like prism C₁ MoSi₁₀ 10c, and the two separated Si atoms surface capped planar Mo₂Si₈ isomer 10d, are optimized, together with the harmonic frequency analysis. The pentagonal antiprism Mo₂Si₁₀ 10a isomer can be seen as the Mo₂ atoms being vertically doped in the pentagonal antiprism Si₁₀ frame. Interestingly, the two Mo₂ atoms in the Mo₂Si₁₀ are bonded together with bond distance of 2.322 Å, which is longer than that (1.975 Å) of the Mo₂ dimer; this result indicates that the Mo–Mo bond is elongated after it is inserted into the Si₁₀ frame due to the interactions among the Mo atoms and Si frame resulting from the charge-transfer which will be discussed below. The C_s 10b isomer is described as the Mo₂ being parallel doped the two pyramidal Si₄ frames. The Mo–Mo bond length in the 10b isomer is longer than that in the 10a isomer, and the C_s 10b isomer is more stable than C_s 10a isomer because the total energy of 10b isomer is lower by 1.026 eV than that of 10a isomer. As for as the C₁ 10c isomer is concerned, it is depicted as one Mo being surface capped on the bipentagonal prism MoSi₁₀ frame; however, the Mo–Mo bond length in the 10c isomer is longer than that in the 10a and 10b isomers, and the total energy of the 10c isomer is lower than those of the 10a and 10b isomers by 1.851 and 0.825 eV, respectively. From our calculated total energies shown in Table

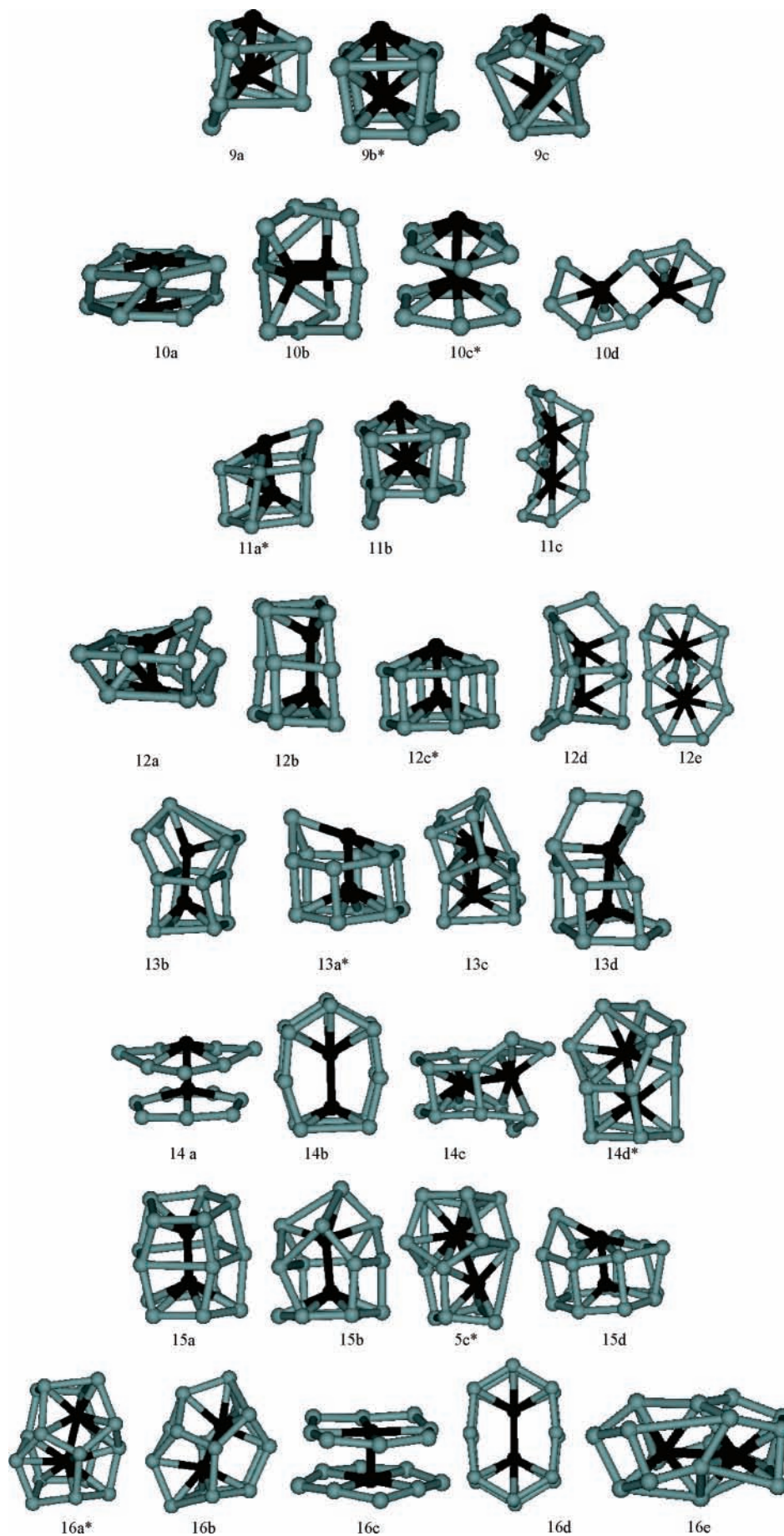


Figure 1. Equilibrium geometries of the Mo_2Si_n ($n = 9-16$) clusters, where the top (or left) Mo atom represents as Mo(1) and the bottom (or right) Mo atom represents Mo(2). Stars indicate the lowest-energy structures of all calculated minima.

TABLE 2: The Calculated Mo–Mo Bond Lengths (Mo–Mo), HOMO, LUMO, HOMO–LUMO Gaps, Total Energies, and Electronic States of the Stable Mo₂Si_n (*n* = 9–16) Clusters

isomer	symmetry	Mo–Mo (Å)	HOMO (hartree)	LUMO (hartree)	HOMO–LUMO (eV)	<i>E_T</i> (hartree)	state
9a	C ₁	2.444	−0.2197	−0.1447	2.063	−169.8874176	¹ A
9b	C_s	2.454	−0.2101	−0.1531	1.566	−169.8876134	¹A'
9c	C _s	2.954	−0.2175	−0.1322	2.345	−169.8712357	¹ A'
10a	C _s	2.322	−0.2170	−0.1507	1.826	−173.7254604	¹ A'
10b	C _s	2.369	−0.2194	−0.1321	2.403	−173.7631692	¹ A'
10c	C₁	2.457	−0.2172	−0.1455	1.972	−173.7934736	¹A
10d	C ₁	3.179	−0.2154	−0.1491	1.825	−173.7149782	¹ A
11a	C₁	2.511	−0.2165	−0.1542	1.715	−177.6754277	¹A
11b	C ₁	2.403	−0.2104	−0.1505	1.648	−177.6752242	¹ A
11c	C ₁	2.847	−0.2200	−0.1569	1.737	−177.6138151	¹ A
12a	C ₁	2.514	−0.2151	−0.1522	1.728	−181.513768	¹ A
12b	C ₁	2.493	−0.2264	−0.1575	1.897	−181.527616	¹ A
12c	C₁	2.355	−0.2046	−0.1301	2.050	−181.5801618	¹A
12d	C ₁	2.644	−0.2196	−0.1581	1.694	−181.5042981	¹ A
12e	C ₁	3.124	−0.2114	−0.1591	1.439	−181.4718664	¹ A
13a	C₁	2.386	−0.2065	−0.1456	1.675	−185.4697197	¹A
13b	C ₁	2.576	−0.2212	−0.1607	1.665	−185.3869664	¹ A
13c	C ₁	2.673	−0.2169	−0.1648	1.434	−185.4162866	¹ A
14a	C ₁	2.328	−0.1997	−0.1519	1.315	−189.2710007	¹ A
14b	C ₁	2.591	−0.2155	−0.1731	1.165	−189.2686962	¹ A
14c	C ₁	2.656	−0.2206	−0.1606	1.649	−189.2884823	¹ A
14d	C₁	2.559	−0.2228	−0.1620	1.672	−189.3170213	¹A
15a	C ₁	2.481	−0.2173	−0.1658	1.413	−193.2052867	¹ A
15b	C₁	2.525	−0.2102	−0.1558	1.494	−193.2089852	¹A
15c	C ₁	2.604	−0.2196	−0.1669	1.450	−193.1906239	¹ A
15d	C ₁	2.352	−0.2084	−0.1518	1.558	−193.1573637	¹ A
16a	C₁	2.484	−0.2212	−0.1647	1.556	−197.1065879	¹A
16b	C _{2v}	2.267	−0.2164	−0.1563	1.649	−197.0936387	¹ A ₁
16c	C ₂	2.204	−0.2214	−0.1250	2.651	−196.9985326	¹ A
16d	C ₁	2.599	−0.2245	−0.1661	1.608	−197.0594728	¹ A
16e	C ₁	3.019	−0.2159	−0.1568	1.625	−197.0315536	¹ A

2, it is confirmed that the 10d isomer, which is seen as two Si atoms being capped on the planar Mo₂Si₈ frame, is weaker in stability as compared to other stable isomers. Consequently, the 10c isomer is selected as the most stable isomer and the ground state for cluster Mo₂Si₁₀. On the basis of the optimized geometries for the Mo₂Si_n (*n* = 9 and 10) clusters (Figure 1), one can find that the diatomic Mo₂ vertically doped Si_n (*n* = 9 and 10) frame are the dominant growth patterns.

Mo₂Si₁₁. Four possible Mo₂Si₁₁ isomers considering various spin configurations are optimized and shown in Figure 1. The 11a and 11b structures, which are generated after one Si atom is surface capped on the 10c isomer, are optimized to be the stable isomers. From the calculated total energies of the 11a and 11b isomers shown in Table 2, the 11a isomer is slightly more stable than the 11b isomer because the total energy of the 11a isomer is a little bit lower than the total energy of the 11b isomer by 0.006 eV. In other words, the 11a and 11b geometries can be seen as the isoenergetic isomers with different geometrical forms. The stable saddle-like 11c isomer is obtained from the 10d geometry, which has a higher total energy comparing with the 11a and 11b isomers. These results reflect that the Mo₂ doped silicon clusters prefer the cagelike structures. Therefore, the opened cagelike geometries are the dominant geometries of the Mo₂Si₁₁ isomers.

Mo₂Si₁₂. Guided by the previous theoretical results on the ground state D_{6h} WSi₁₂²⁵ and Mo₂Si_n (*n* = 10 and 11) clusters described as above, three Mo₂Si₁₂ isomers, emerging from one Si atom being surface-capped on the small-sized Mo₂Si_n (*n* = 10, 11) clusters, are obtained and shown in Figure 1. From the findings related to the geometries of the examined systems, the 12a isomer is generated with the serious distortion of the Mo₂ dimer inserted into the irregular hexagonal prism Si₁₂ frame with Mo–Mo bond length of 2.514 Å. As for the 12b isomer, it can be described as the Mo₂ dimer being encapsulated into

the distorted tetragonal prism *D*_{4h} Si₁₂. However, from the calculated total energies shown in Table 2, the 12b isomer is more stable than the 12a isomer does. The stable 12c isomer can be seen as one Mo atom being surface capped on the hexagonal prism MoSi₁₂ cluster.³ Furthermore, the 12c isomer is relatively more stable than the 12b isomer because the total energy of 12c isomer is lower by 1.43 eV than that of 12b isomer does (see Table 2). The 12d isomer is seen as an irregular structure and the 12e geometry is obtained with one Si atom being surface-capped on the 11c structure. According to the calculated total energies tabulated in Table 2, it is noticed that the 12e isomer has higher total energy and is less stable than other isomers; consequently, the 12c isomer is the lowest-energy isomer and the ground state for Mo₂Si₁₂ cluster. This finding indicates that the Mo₂ doped Si₁₂ isomer has the framework that is analogous to the single W atom doped Si₁₂ frame.²⁵

Mo₂Si₁₃. A variety of possible initial geometries are optimized for the Mo₂Si₁₃ cluster and shown in Figure 1. It should be pointed out that the hexagonal prism 13a isomer with one Si atom being parallel surface-capped on the prism Mo₂Si₁₂ 12c frame is turned out to be the most stable structure (Table 2). The 13b isomer, which can be described as the distorted prism *D*_{4h} symmetry, is born after one Si atom is surface capped on the 12b isomer and essentially maintains the analogous framework of the 12b cluster upon adding one silicon atom. The 13c isomer, which is obtained after three Si atoms are surface capped on appropriate sites of the 10c isomer, is optimized to be a stable isomer. However, it is noticed that the 13c and 13b isomers are 1.454 and 2.252 eV higher in total energies than the 13a isomer has, which indicates that the Mo₂ encapsulated Si₁₃ frame is not the dominant geometry of the Mo₂Si₁₃ clusters. Furthermore, the growth pattern of the small-sized Mo₂ doped Si_n (*n* ≤ 13) clusters is similar to that of the Mo doped Si_n frames, and the opened cagelike geometries are the dominant structures.

Mo₂Si₁₄. Starting from various initial structures, the Mo₂Si₁₄ cluster is calculated by considering with different spin configurations. Four isomers are identified for the Mo₂Si₁₄ cluster, which are the distorted heptagonal prism 14a isomer with Mo₂ dimer acting as the symmetrical axis, the heptagonal prism 14b isomer with Mo₂ dimer vertically to the prism symmetrical axis, the seriously distorted heptagonal prism 14c isomer, and the cage-like C₁ 14d isomer, respectively, shown in Figure 1.

Two remarkable Mo₂ encapsulated sandwich-like silicon isomers, namely, 14a and 14b, are formed. The 14a geometry with Mo₂-encapsulated sandwich-like heptagonal prism *D*_{7h} Si₁₄ frame is considered; however, the final optimized geometry reveals that the Mo₂ atoms in the Mo₂Si₁₄ isomer move from the center sites of the Si₁₄ frame to the each center site of the planar Si₇ unit and the Mo–Mo bond length of the Mo₂ dimer is finally elongated under the interaction between two Si₇ units because the Si–Mo interactions are stronger than the Mo–Mo interaction as mentioned above. However, there is a stable structure where the Mo₂ atoms can be vertically encapsulated into the sandwich-like or boat-like Mo₂Si₁₄ 14b geometry with Mo₂ dimer vertically to the symmetrical axis of two Si₇ units. In addition, the 14c isomer is the derivative of the 14b isomer and is more stable than the 14b isomer with the difference of the total energies being 0.538 eV. As observed from the optimized geometries and energies in Table 2, it can be seen that the lowest-energy isomer is a compressed quadrangular prism Mo₂Si₁₄ 14d structure, which is described as the Si₂ dimer being surface capped on the top of the slight distorted 12b geometry. Furthermore, the dominant geometries of the Mo₂-Si₁₄ isomers are the Mo₂ encapsulated Si₁₄ structures which are different from the Mo₂ doped cage-like opened Si_n (*n* ≤ 13) isomers while the sandwich-like 14a and 14b geometries are not the dominant geometries. Our results show that the Mo₂Si_n (*n* ≤ 13) geometries are the cage-like opened isomers while the Mo₂Si_n (*n* ≥ 14) geometries are the cage-like closed isomers, and consequently, the structure transition occurs at *n* = 14.

Mo₂Si₁₅. The optimized geometries indicate that the possible Mo₂Si₁₅ isomers with high symmetries are not the stable structures. However, after undergoing the slight distortion of the Mo₂Si₁₅ geometry to the low symmetry, the stable C₁ 15a isomer is finally obtained (Figure 1). The cage-like pentagonal prism 15a isomer is described as the Mo₂ dimer being parallel inserted to the pentagonal Si₁₅ frame with Mo–Mo bond length of 2.481 Å, which indicate that the Mo₂Si₁₅ geometry is composed of the two sandwich-like MoSi₁₀ units and the Mo–Mo bond length in this isomer is longer than that in the free Mo₂ dimer. In this isomer the attractive interactions between each Si₁₀ unit and Mo atom are stronger than the interaction between Mo and Mo atoms. It is worth to point out that the 15a and 15b can be seen as the degenerated isomers in energy because from Table 2 the difference of total energies between them is very small. As for as the deformed cage-like 15b and 15c isomers are concerned, the two isomers are described as the diatomic Mo₂ dimer being encapsulated into the Si₁₅ frame; furthermore, the 15b cage is more stable than the 15c cage because as shown in Table 2 the total energy of isomer 15b is lower than that of isomer 15c by 0.50 eV. In addition, the 15d isomer is considered, which is generated when one Si atom is surface-capped on the heptagonal prism 14a isomer, to form sandwich-like structure. But the sandwich-like 15d isomer is higher in total energy than the 15b and 15c isomers by respective 1.505 and 0.905 eV. Therefore, the stability of Mo₂ doped prism-like Si₁₅ geometry is weaker than the Mo₂ encapsulated caged Si₁₅ geometry in which the Mo₂ atoms in the cage-like

geometries interact with more silicon atoms simultaneously with unequal Mo–Si bond lengths and try to terminate the dangling bonds of the silicon atoms with delocalized covalent bonds. Inspection of the calculated total energies of the Mo₂-Si₁₅ isomers from Table 2, we can find that the 15b isomer is the lowest-energy structure, and corresponds to the ground state of this size (*n* = 15) cluster.

Mo₂Si₁₆. As for as the Mo₂Si₁₆ 16a isomer is concerned, the geometry can be described as the Mo₂ dimer being encapsulated into the slight distorted cage-like *D*_{4d} Si₁₆ frame. Furthermore, the doped Mo–Mo bond length in the 16a cluster is 2.484 Å, which is longer than the free quintet diatomic bond length of 2.141 Å with electronic state of ⁵Σ_g. Because the attractive interactions between Mo₂ and Si₁₆ frame are stronger than that between Mo and Mo atoms, and the Mo₂ dimer is finally dissociated under the attractive interactions of Mo₂ dimer and Si₁₆ frame, the formed 16a isomer is composed of the two sandwich-like MoSi₈ units. From the calculated total energy for Mo₂Si₁₆ isomers in Table 2, obviously, the 16a geometry is the lowest-energy isomer. The C_{2v} Mo₂Si₁₆ 16b isomer is obtained after the Mo₂ dimer is inserted to the Si surface-capped distorted 15a frame. However, the 16a isomer is more stable than the 16b isomer because as shown in Table 2 the total energy of 16b isomer is higher than that of 16a isomer by 0.352 eV. Guided by above investigations on the 14a and 14b isomers, the striking 16c and 16d isomers are also considered. The C₂ 16c isomer is depicted as the Mo₂ isomer being parallel inserted into the octagonal prism Si₁₆ frame, in turn, the final obtained 16c geometry is composed of the two planar-like MoSi₈ units with electronic state of ¹A; and the Mo–Mo bond length being 2.204 Å which is slightly longer than the free Mo₂ bond length. From Table 2 it can be seen that the 16c isomer is higher in total energy than the 16a and 16b isomers by 2.940 and 2.588 eV respectively. As a consequence, the layered 16c structure is not the most stable building block for the formation of new materials. The 16d isomer is depicted as the Mo₂ isomer being vertically inserted the sandwich-like octagonal prism-like Mo₂-Si₁₆ structure. Interestingly, this structure is less stable than the 16a isomer and is not selected as the ground state and building block of new material with novel properties. Therefore, the sandwich-like 16c and 16d isomers are not the dominant geometries after examined by the calculated total energies. In addition, the irregular 16e isomer is also considered and optimized as the stable geometry, but its total energy is obviously higher than that of the encapsulated 16a structure has.

According to the above discussions, one can conclude that the stable layered sandwich-like structures are not the most stable structures and cannot be seen as the building block for bulk material and nanotube. As for the most stable bimetal Mo₂ encapsulated silicon clusters, it shows that the opened cage-like Mo₂Si_n (*n* ≤ 13) clusters, which are based upon the MoSi₁₀ and MoSi₁₂ clusters, are the dominant geometries for the middle-sized clusters while the Mo₂ encapsulated silicon clusters are the dominant geometries for the large-sized clusters.

3.2. The Relative Stabilities. In order to investigate the relative stabilities of the most stable Mo₂Si_n (*n* = 9–16) clusters, it is significant to calculate the averaged atomic binding energies for the Mo₂Si_n clusters (*E*_b(*n*)) and the fragmentation energies (*D*(*n*, *n* – 1)) with respect to removal of one Si atom from the most stable Mo₂Si_n clusters. The averaged atomic binding energies and fragmentation energies of the Mo₂Si_n (*n* = 9–16) clusters are defined as

$$D(n, n-1) = E_T(\text{Mo}_2\text{Si}_{n-1}) + E_T(\text{Si}) - E_T(\text{Mo}_2\text{Si}_n)$$

$$E_b(n) = [2E_T(\text{Mo}) + nE_T(\text{Si}) - E_T(\text{Mo}_2\text{Si}_n)]/(n+2)$$

where $E_T(\text{Mo}_2\text{Si}_{n-1})$, $E_T(\text{Si})$, $E_T(\text{Mo})$, and $E_T(\text{Mo}_2\text{Si}_n)$ denote the total energies of the respective Mo₂Si_{n-1}, Si, Mo, and Mo₂Si_n clusters. The calculated $E_b(n)$ and $D(n, n-1)$ values of the most stable Mo₂Si_n (*n* = 9–16) isomers are plotted as the curves of E_b and $D(n, n-1)$ against the corresponding number of the Si atoms in Figure 2 and Figure 3 and also summarized in Table 3. It should be mentioned that the features of the size-evolution are intuitively viewed and the peaks of the curves correspond to those clusters have enhanced local stabilities.

The averaged atomic binding energies of the Mo₂Si_n clusters are calculated, which are listed in Table 3 and shown in Figure 2. The curve in Figure 2 shows the similar tendency to the calculated fragmentation energies (Figure 3) except for *n* = 13, indicating that the predicted relative stabilities of the Mo₂Si_n vary synchronously with the cluster size.

According to the calculated fragmentation energies shown in Figure 3 and Table 3, two remarkable peaks at *n* = 10 and 12 for the Mo₂Si_n (*n* = 9–16) clusters are found, showing that the corresponding clusters have slightly stronger relative stabilities and have large abundances in mass spectroscopy as compared to the corresponding neighbors. From Figures 2 and Figure 3, the particularly most stable geometry can be assigned to the cluster of Mo₂Si₁₀, which is slightly higher in fragmentation energy than the Mo₂Si₁₂. Interestingly, these findings of the bimetal Mo₂ doped silicon clusters are slightly different from those of the single TM doped silicon clusters.³¹ This finding, underlining once more the prominent role of the Si₁₀ matrix, is relevant for the architecture of metal–silicon clusters. It is indicated that the Mo₂Si₁₀ cluster is treated more thoroughly in the context of the previous literature on clusters of the form TMGe₁₀,⁸ since the Mo₂Si₁₀ cluster addresses the case of multiple metal impurities. Furthermore, the calculated fragmentation energies in term of the 10c isomer show that it has the strongest stability of all Mo₂Si₁₀ isomers, reflecting that the prismatic structures are the preferred geometries. According to the calculated total energies of the Mo₂Si₁₅ isomers, it is noticed that the 15a isomer can act as the building block for the novel material because it is the most stable isomer which is composed of two MoSi₁₀ 10c units. The calculated ionization potentials (IPs) for the Mo₂Si_n (*n* = 12, 13, and 14) clusters are 6.43, 6.72, and 7.13 eV, respectively. The obtained results reflect that the Mo₂Si₁₄ cluster has the strongest chemical stability.

3.3. Population Analysis. The net Mulliken populations (MP) and Natural populations (NP) of the Mo atoms in the most stable Mo₂Si_n isomers are listed in Table 4, the Mo(1) and Mo(2) are defined as in Figure 1, both the MP and NP for the most stable Mo₂Si_n isomers draw the consistent conclusion. The net MP and NP values for the Mo atoms in the Mo₂Si_n (*n* = 9–16) clusters are negative except the MP of the Mo(1) in the 10c isomer (Table 4), showing that the charges in the corresponding clusters transfer from the Mo atoms to the Si_n frames. And the unsaturated d orbitals of Mo atoms obtain the electrons from the Si atoms and S orbitals of Mo atoms, which is also clearly shown in Table 5. These results are coincidence with previous findings on ReSi_n and WSi₁₅.^{27,30} As the general trend, the MP as well as 4d orbital populations of Mo(1) and Mo(2) are first increased to some certain values then decreased. However, the NP and 4d orbital populations of Mo(2) atom are gradually increased as the number of Si atoms increasing. Interestingly, the 5s orbital populations of the Mo atoms are independent of the size of the clusters because they vary very small. It should

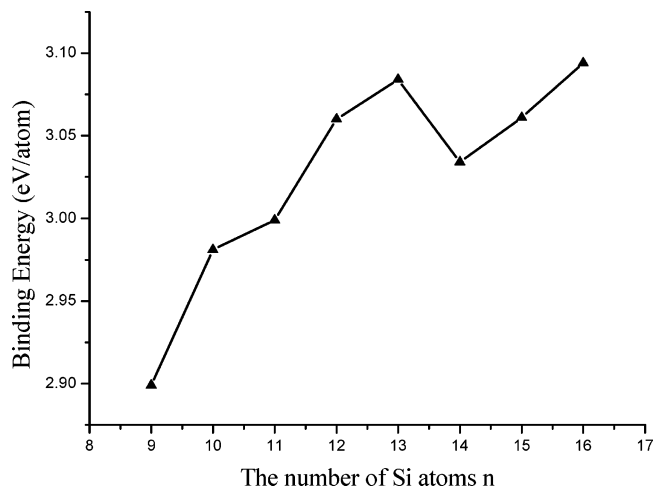


Figure 2. Size dependence of the averaged atomic binding energies of the most stable Mo₂Si_n clusters.

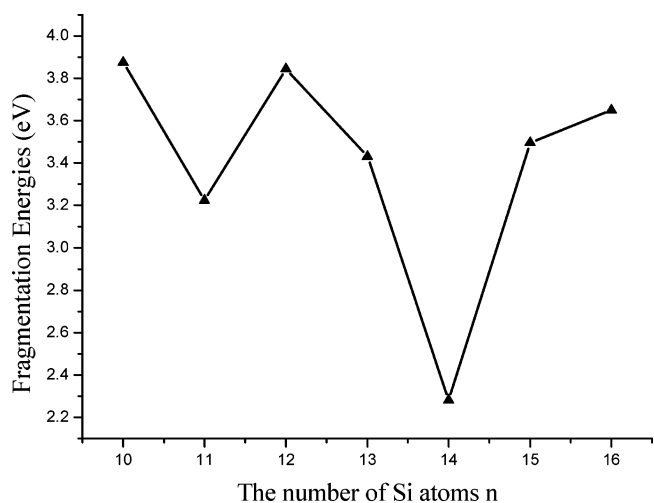


Figure 3. Size dependence of the fragmentation energies of the most stable Mo₂Si_n clusters.

TABLE 3: The Calculated Fragmentation Energies ($D(n, n-1)$) and the Averaged Atomic Binding Energies (E_b) of the Most Stable Mo₂Si_n (*n* = 9–16) Clusters (Unit: eV)

size (<i>n</i>)	9	10	11	12	13	14	15	16
$D(n, n-1)$	3.874	3.224	3.844	3.431	2.281	3.496	3.650	
E_b	2.899	2.981	2.999	3.060	3.084	3.034	3.061	3.094

TABLE 4: Mulliken and Natural Populations of the Mo Atoms of the Most Stable Mo₂Si_n (*n* = 9–16) Systems, Where the Mo(1) and Mo(2) Correspond to the Top (or Left) Mo and Bottom (or Right) Mo Atoms in Figure 1

isomer	Mo(1)		Mo(2)	
	MP	NP	MP	NP
9a	-0.869	-0.344	-2.112	-1.437
10c	0.1099	-0.4058	-1.1944	-1.5400
11a	-1.4350	-0.5663	-2.2982	-1.6636
12c	-0.9287	-0.2165	-2.4364	-1.5178
13a	-0.0720	-0.3455	-1.0097	-1.4585
14d	-1.7822	-1.2927	-2.0947	-1.6547
15a	-2.4850	-1.7451	-2.3260	-1.6905
16a	-2.2132	-1.4206	-2.3890	-1.7138

be pointed out that the encapsulated Mo atoms in the most stable Mo₂Si_n (*n* = 9–16) clusters obtain more charges from their surroundings than the surface-capped Mo atoms do, and that the encapsulated Mo atom has a tendency to interact with more silicon atoms with unequal bond lengths and try to

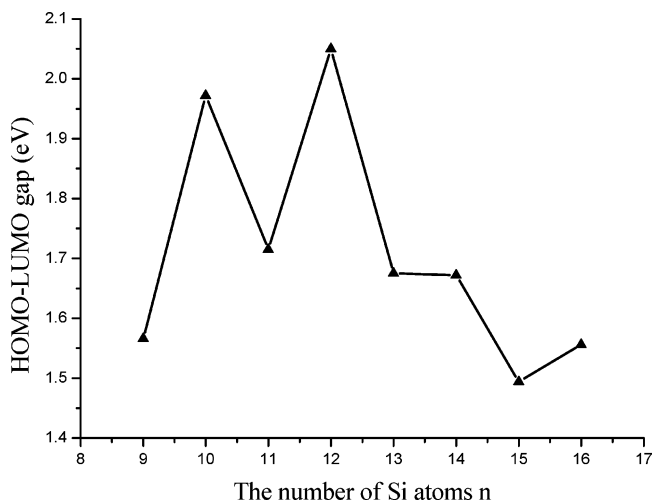
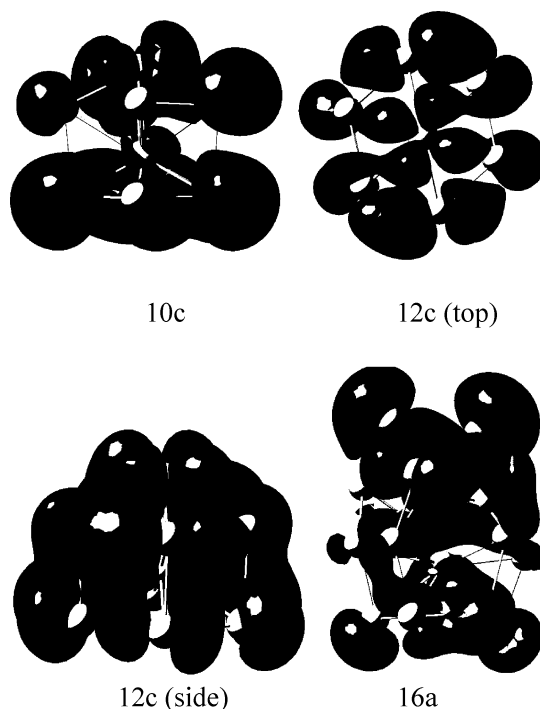
TABLE 5: The Natural Electronic Configurations of the Mo Atoms in the Most Stable Mo₂Si_n (*n* = 9–16) Systems

isomer	Mo(1)		Mo(2)	
	5s	4d	5s	4d
9b	0.30	6.01	0.39	6.89
10c	0.27	6.08	0.40	6.99
11a	0.31	6.18	0.39	7.12
12c	0.19	5.98	0.34	6.97
13a	0.29	5.98	0.33	6.94
14d	0.35	6.82	0.34	7.17
15a	0.35	7.26	0.36	7.19
16a	0.34	6.96	0.32	7.22

terminate the dangling bonds of silicon atoms. Therefore, the doped Mo atoms play very important roles in the stabilities of the Mo₂Si_n (*n* = 9–16) clusters.

3.4. HOMO and LUMO Properties. The HOMO and LUMO energies as well as the corresponding HOMO–LUMO gaps of the Mo₂Si_n clusters are tabulated in Table 1. Based on our calculated results, it can be seen that for the most stable Mo₂Si_n (*n* = 9, 11, 13–16) clusters the HOMO–LUMO gaps are about 1.6 eV while the Mo₂Si₁₂ cluster has the biggest gap, which is reflected in Figure 4. In other words, the chemical stability of the Mo₂Si₁₂ clusters is stronger as compared with its neighbors, and the Mo₂Si₁₂ cluster has enhanced chemical stability. Therefore, Having strong relative stability and chemical stability, the Mo₂Si₁₂ cluster can be seen as the most stable building block and can be selected as candidate of novel nanomaterials. As for as the Mo₂Si₁₀ cluster is concerned, it is worth to point out that the HOMO–LUMO gap of the Mo₂Si₁₀ being 1.972 eV is slightly smaller than that (2.05 eV) of the Mo₂Si₁₂ cluster and therefore the Mo₂Si₁₂ cluster is slightly stronger in chemical stability than the Mo₂Si₁₀ cluster does. Furthermore, we can predict that the HOMO–LUMO gaps for the Mo₂Si₁₀ and Mo₂Si₁₂ clusters can be detachable experimentally. Consequently, the Mo₂Si₁₀ and Mo₂Si₁₂ clusters are stable in ionization and dissociation process and contribute to forming the most stable Mo₂-doped silicon nanoclusters, and make them more attractive for the cluster-assembled nanomaterial.

The contour map of the HOMO for the most stable Mo₂Si₁₀ isomer is displayed in Figure 5. It can be seen from the Figure 5 that some π -type and σ -type bonds are formed among the Si_n atoms. The encapsulated Mo atom in the Mo₂Si₁₀ interacts with 10 silicon atoms simultaneously and terminates the dangling bonds of silicon atoms while the surface capped Mo atom tries to interact with its neighbor silicon atoms with σ -type bonds.

**Figure 4.** Size dependence of HOMO–LUMO gap of the most stable Mo₂Si_n clusters.**Figure 5.** The contour maps of the HOMO for the most stable 10c, 12c, and 16a isomers.

As far as the property of the HOMO of the Mo₂Si₁₂ cluster (Figure 5) is concerned, the π -type bonds are formed among the Si_n atoms, which are distributed beside Mo₂ atoms, and correspond to the delocalized π -type bonds. Furthermore, the encapsulated Mo atom obtains more charges from its bonded silicon atoms and interacts with silicon atoms by relatively weaker d-s σ -type bonds.³ However, the surface-capped Mo atom have more unfilled d orbitals and try to form the stronger σ -type bonds with its neighbor silicon atoms as compared to the encapsulated Mo atom. From the contour map of the HOMO for the Mo₂Si₁₆ cluster shown in Figure 5, it can be obviously seen that each encapsulated Mo atom is surrounded by eight silicon atoms simultaneously, and that the Mo₂ atoms and silicon atoms form the delocalized π -type bonds. Only a few Si–Si bonding contributes to the π -type bonds because the σ -type bonds are the dominant Si–Si bonding type. It should be mentioned that our results show that the Si–Si bonds of the most stable Mo₂Si₁₆ cluster is not regular comparing with those Si–Si bonds in the Mo₂Si₁₂ cluster.

4. Conclusions

The systematic investigations on the geometrical and electronic properties as well as the growth patterns of the Mo₂Si_n (*n* = 9–16) clusters have been performed theoretically at the (U)B3LYP/LanL2DZ level. All calculated results can be summarized as follows: (1) The most stable Mo₂Si_n clusters in term of the optimized geometries show that the cage-like Mo₂Si_n (*n* = 9–16) clusters are the dominant structures, and within them the Mo atoms prefer to interacting with more silicon atoms. The Mo–Mo distance in these clusters are elongated as compare to the Mo–Mo distance in the free Mo₂ dimer because the Mo–Si interactions are stronger than the Mo–Mo interaction. In the Mo₂Si_n clusters the Si–Si and Mo–Si interactions play more important roles as compared to the Mo–Mo interaction. In other words, the Si–Si and Mo–Si interactions take the dominant effects to the stabilities of the clusters. (2) According to the optimized geometries, the lowest-energy structures feature one

Mo atom inside a Si cage and another one Mo atom on the surface at smaller sizes. As for $n = 14$ and larger, however, both Mo atoms are encapsulated by Si atoms. It is interesting that the Mo₂Si_n clusters undergo a structural transition at $n = 14$. (3) The relative stabilities of the Mo₂Si_n ($n = 9–16$) in term of calculated fragmentation energies are discussed. Our results show that the local maximums of the stabilities of the Mo₂Si_n clusters are the clusters with $n = 10$ and 12, and the Mo₂Si₁₀ is the most stable structure. (4) Based upon the calculated natural populations and natural electronic configurations, it is noticed that the charges are transferred from silicon atoms to the 4d orbitals of the Mo₂ atoms. (5) The calculated HOMO and LUMO energies as well as the HOMO–LUMO gaps indicate that the most stable Mo₂Si₁₀ and Mo₂Si₁₂ clusters have larger HOMO–LUMO gaps and have stronger chemical stabilities as compared to their neighbor size of clusters.

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